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Thomas I. Wallow
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2 Negative Tone Processing
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Plamen Tzviatkov, FUJIFILM Electronic Materials U.S.A., Inc. (United States)

3 EUV: Joint Session with Conference 8322
Yoshio Kawai, Shin-Etsu Chemical Co., Ltd. (Japan)

4 Optical Extensions
Ralph R. Dammel, AZ Electronic Materials USA Corporation (United States)
Clifford L. Henderson, Georgia Institute of Technology (United States)

5 Directed Self-Assembly I: Resist Processing: Joint Session with Conference 8323
Daniel P. Sanders, IBM Almaden Research Center (United States)

6 Simulation of Resist Processes
Clifford L. Henderson, Georgia Institute of Technology (United States)
Todd R. Younkin, Intel Corporation (Belgium)

7 Resist Fundamentals
Plamen Tzviatkov, FUJIFILM Electronic Materials U.S.A., Inc. (United States)
Luisa D. Bozano, IBM Almaden Research Center (United States)

8 Novel Materials and Processing I
Ramakrishnan Ayothi, JSR Micro, Inc. (United States)
Douglas J. Guerrero, Brewer Science, Inc. (United States)

9 Lithography at the Intersection of Optics and Chemistry: Joint Session with Conference 8326
Mark H. Somervell, Tokyo Electron America, Inc. (United States)
Will Conley, Dynamic Intelligence (United States)

10 EUV Materials, Processing, and Analysis
Christoph K. Hohle, Fraunhofer-Center Nanoelektronische Technologien (Germany)
Nobuyuki N. Matsuzawa, Sony Corporation (Japan)

11 Novel Materials and Processing II
Dah-Chung Owe-Yang, Shin-Etsu MicroSi, Inc. (United States)
George G. Barclay, Dow Advanced Materials (United States)